

a plurality of element isolation films formed such as to have a predetermined uniform depth from a main surface of said semiconductor substrate, said element isolation films dividing the area from said main surface to said depth into a plurality of first regions;

first wells formed in said first regions, respectively; and

E! a second well formed in a second region deeper than each of said first wells in said semiconductor substrate, said second well being in contact with some of said first wells to provide electrical connection therebetween and not being in contact with said first wells adjacent to said some of said first wells,

wherein said first and second wells of said first and second regions on one side with reference to a predetermined boundary are of a first conductivity type, and said first wells on the other side are of a second conductivity type, and

wherein said second well is formed only on one side of said second region with reference to the predetermined boundary.

REMARKS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 1, 3, 5-12, 15, 16, 19, 20 and 22-24 are pending in the present application. Claim 16 has been amended by the present amendment.

In the outstanding Office Action, the drawings were objected to; Claims 16 and 23 were rejected under 35 U.S.C. § 102(b) as anticipated by Manning; Claims 1, 5, 15, 20, 22 and 24 were allowed; and Claim 19 was indicated as allowable if rewritten in independent form.

Applicants thank the Examiner for the indication of allowable subject matter.